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Analog Power AMF920NE

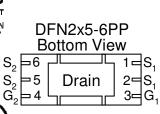
#### Dual N-Channel 20-V (D-S) MOSFET

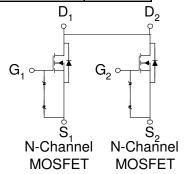
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
$V_{DS}(V)$	$V_{DS}(V)$ $\eta_{DS(on)} m(\Omega)$				
20	$22 @ V_{CS} = 4.5V$	11			
20	$28 @ V_{CS} = 2.5V$	9.2			

#### ROHS COMPLIANT

- Low r<sub>DS(on)</sub> provides higher efficiency and HALOGEN extends battery life
- Low thermal impedance copper leadframe DFN2x5-6PP saves board space
- Fast switching speed
- High performance trench technology





ESD Protected
2000V

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)							
Parameter Parameter			Limit	Units			
Drain-Source Voltage			20	v			
Gate-Source Voltage			± 12	V			
	T <sub>A</sub> =25°C	${ m I_D}$	11				
Continuous Drain Current <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	<sub>ID</sub>	8.5	A			
Pulsed Drain Current <sup>b</sup>			±40				
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	3.1	Α			
D D: a	$T_A=25^{\circ}C$	D	3.5	w			
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	$\mathbf{r}_{\mathrm{D}}$	1.8	••			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
a	t <= 10 sec	D	36	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	$R_{\theta JA}$	76	°C/W		

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
D			Limits			T	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{\mathrm{DS}} = V_{\mathrm{GS}}, I_{\mathrm{D}} = 250\mathrm{uA}$	0.5				
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±10	uA	
Zara Cata Valtaga Drain Current	I <sub>DSS</sub>	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			30		
On-State Drain Current <sup>A</sup>	ID(on)	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	20			Α	
		$V_{GS} = 4.5 \text{ V}, I_D = 6.7 \text{ A}$	10	18	22		
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4 \text{ V}, I_D = 5.6 \text{ A}$	10.5	19	23	mΩ	
		$V_{GS} = 2.5 \text{ V}, I_D = 4.5 \text{ A}$	11	23	28		
Forward Tranconductance <sup>A</sup>	$g_{\mathrm{fs}}$	$V_{DS} = 15 \text{ V}, I_D = 6 \text{ A}$		22		S	
Diode Forward Voltage	$V_{ m SD}$	$I_S = 0.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$		9.2		nC	
Gate-Source Charge	$Q_{gs}$	VDS = 10  V,  VGS = 4.3  V, $ID = 6  A$		1.9			
Gate-Drain Charge	Qgd	1D = 0 A		2.8			
Turn-On Delay Time	t <sub>d(on)</sub>			1.7			
Rise Time	tr	$V_{\rm DD}$ = 10 V, $R_{\rm L}$ = 15 $\Omega$ , $I_{\rm D}$ = 1 A,		2.3		$\frac{1}{nS}$	
Turn-Off Delay Time	td(off)	$V_{GEN} = 4.5 \text{ V}$		1.1			
Fall-Time	$t_{\mathrm{f}}$			4.4			

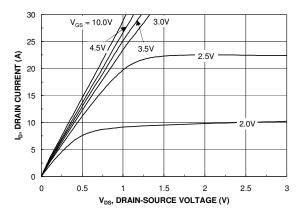
#### Notes

- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

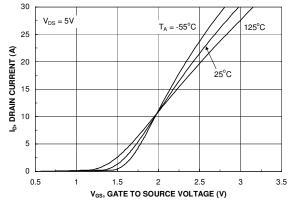
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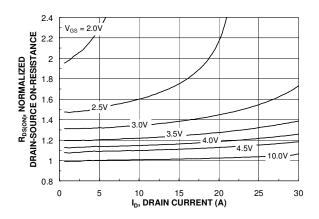
## Typical Electrical Characteristics (N-Channel)



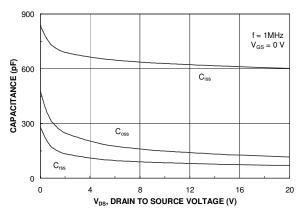
**Output Characteristics** 



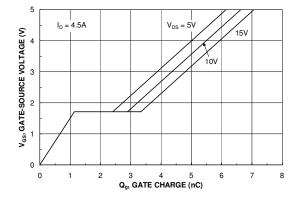
**Transfer Characteristics** 



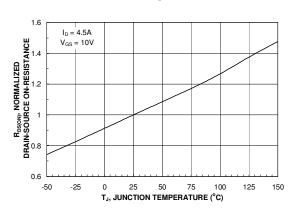
On-Resistance vs. Drain Current



Capacitance



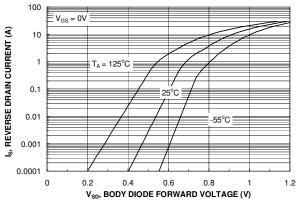
**Gate Charge** 

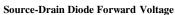


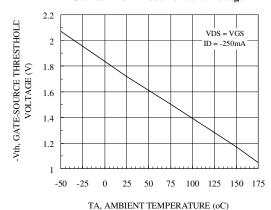
On-Resistance vs. Junction Temperature

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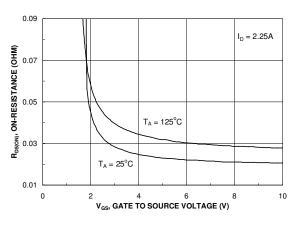
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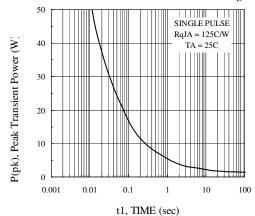




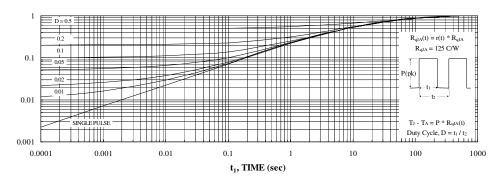
Vth Gate to Source Voltage Vs Temperature



On-Resistance vs. Gate-to-Source Voltage



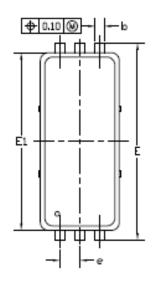
Single Pulse Power, Junction-to-Ambient

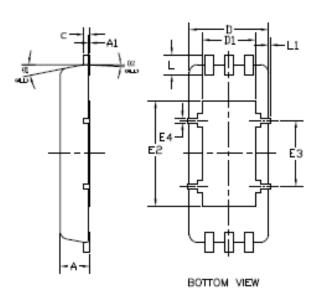


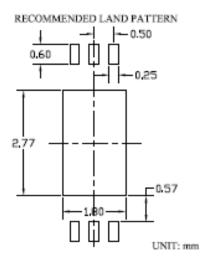
**Normalized Thermal Transient Junction to Ambient** 

# Package Information

DFN2x5\_6L\_EP1\_P PACKAGE OUTLINE







SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
	MIN	NOM	MAX	MIN	NOM	MAX	
Α.	0.70	0.75	0.80	0.028	0.030	0.031	
A1	0.00		0.05	0.000		0.002	
ъ	0.20	0.23	0.30	0.008	0.009	0.012	
c	0.10	0.15	0.20	0.004	0.006	0.008	
D	2. 00 BSC			0,079 BSC			
D1	1.30	1.35	1.55	0.051	0.053	0.061	
E	5. 00 BSC			0. 197 BSC			
El	4. 50 BSC			0.177 BSC			
E2	2.60	2.67	2.95	0.102	0.105	0.116	
E3	1.67 BSC			0.066 BSC			
E4	0.13 RSC			0.005 BSC			
e	0.50 BSC			0.020 BSC			
L	0.40	0.50	0.60	0.016	0.020	0.024	
L1	0		0.10	0	_	0.004	
01	0.0	10°	12°	0,0	10°	120	
82		3° BSC			3º BSC		

#### NOTE

- PAKCAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
   MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MIL EACH.
- CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.